

LIST OF PUBLICATIONS

1. Baskaran Subramanian, Mohanbabu Anandan, Saminathan Veerappan, Murugapandian Panneerselvam, Mohammed Wasim, **Saravana Kumar Radhakrishnan**, Praveen Pechimuthu, Yogesh Kumar Verma, Subash Navaneethan Vivekanandhan 2020, Switching Transient Analysis and Characterization of an E-Mode B-Doped GaN-Capped AlGa_N DH-HEMT with a Freewheeling Schottky Barrier Diode (SBD), Journal of Electronic Materials, Vol: 49, PP 4091-4099. (Impact Factor -1.777), (Publisher : Springer)
2. P. Murugapandian, A. Mohanbabu V, Rajya Lakshmi V, N. Ramakrishnan, Arathy Varghese, MOHD Wasime, S. Baskaran, **R. Saravana Kumar**, V. Janakiraman 2020, Performance analysis of HfO₂/InAlN/AlN/GaN HEMT with AlN buffer layer for high power microwave applications Journal of Science: Advanced Materials and Devices, Vol. 5, No. 2, pp 192 – 198. (Impact Factor- 3.36), (Publisher : Elsevier).
3. R. Poornachandran, N. Mohankumar, **Saravana Kumar R** & S. Baskaran 2020 ‘Noise analysis of double gate composite InAs based HEMTs for high frequency applications” Journal of Microsystems Technologies. (Impact Factor -1.7), (Publisher : Springer)
4. R. Poornachandran, N. Mohankumar, **Saravana Kumar R** & G. Sujatha 2019, ‘Analysis of microwave noise in an enhancement-mode dual-quantum-well InAs HEMT’, Journal of Computational Electronics. (Impact Factor -1.526), (Publisher : Springer)
5. Poornachandran R, Mohankumar N, **Saravana Kumar R** & Sujatha G 2019 ‘Sheet carrier density and I-V analysis of In_{0.7}Ga_{0.3}As/InAs/In_{0.7}Ga_{0.3}As dual channel double gate HEMT for THz applications’, International Journal of Numerical Modelling, Vol. 32, No. 5. (Impact Factor - 0.795), (Publisher : John Wiley & Sons, Ltd)
6. **Saravana Kumar R**, Mohanbabu A, Mohankumar N & Godwin Raj D 2018, ‘Simulation of InGaAs Sub-channel DG-HEMT for analogue / RF applications’, International Journal of Electronics. vol. 105, no. 3, pp.446-456. ISSN: 0020-7217. (Impact Factor- 0.729), (Publisher : Taylor & Francis).

7. **Saravana Kumar R**, Baskaran S, Mohanbabu A & Mohankumar N 2018, 'Comparative assessment of InGaAs sub-channel and InAs composite channel Double gate (DG)-HEMT for Sub-millimeter wave applications', AEU-International Journal of Electronics and Communications, vol. 83, pp. 462-469. (Impact Factor- 1.147), (Publisher : Elsevier).
8. **Saravana Kumar R**, Mohanbabu A, Mohankumar N & Godwin Raj D 2017, 'In_{0.7}Ga_{0.3}As/InAs/In_{0.7}Ga_{0.3}As Composite Channel Double Gate (DG)-HEMT Devices for High-Frequency Applications', Journal of Computational Electronics, vol. 16, no. 3, pp. 732-740. (Impact Factor -1.526), (Publisher : Springer)
9. Mohanbabu A, **Saravana Kumar R** & Mohankumar N, 2017, 'Noise Characterization of enhancement mode ALGaN graded barrier MIS-HEMT devices', Superlattices and Microstructures. vol. 112, pp 604-618. (Impact Factor- 2.09), (Publisher : Elsevier).
10. **Saravana Kumar R**, Sarathi A & Ramesh C 2016, 'Characterization of single and DG InSb HEMT devices for High frequency applications', International Journal of Innovative Research in Science Engineering & Technology, vol. 5, no. 4, pp 6319-6325.
11. **Saravana Kumar R** & Sarathi A 2015, 'Characterization of InAs Composite channel M-HEMT for THz Frequency applications', International Journal of Innovative Research in Science Engineering and Technology, vol. 4, no. 5, pp 3550-3555.